

4. CMOS 2 input multiplexer:

In the complementary mos transistor in a 2 input  $I_0$  and  $I_1$ , give the output is  $F$ .

2x1 Mux

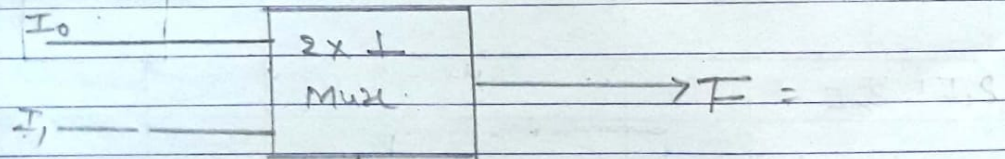


fig (a) Symbol of 2x1 mux

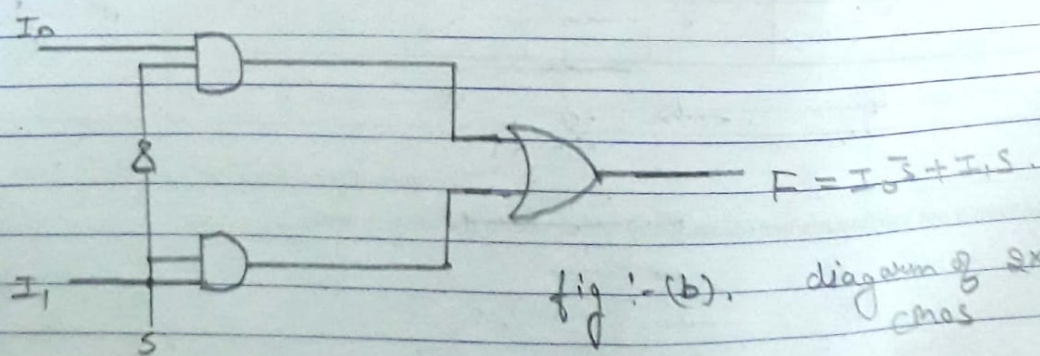


fig :- (b).

diagram of 2x1 mux CMOS

$$F = I_0 \bar{S} + I_1 S$$

$$F = \bar{F} = \overline{I_0 \bar{S} + I_1 S}$$

$$F = \overline{I_0 \bar{S}} \cdot \overline{I_1 S}$$

$$F = (\bar{I}_0 + S) \cdot (\bar{I}_1 + \bar{S}_1) \quad \text{--- } \textcircled{1}$$

or equation  $\textcircled{1}$  to draw the CMOS & XL Mux diagram.

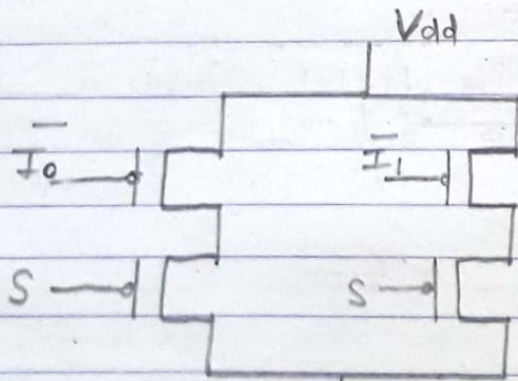
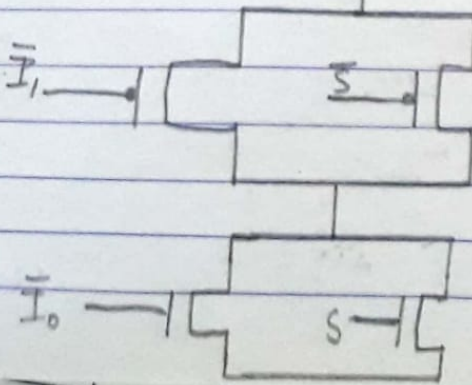


fig (c) CMOS & XL Multiplexer diagram



### 5.1. Memory latch CMOS logic circuit.

In the CMOS latching the ~~transi~~ data in transmission gate and drain the latch the feedback and hold the data at this point. The CMOS latching is more types Flip-Flop.

1. RS Flip Flop.
2. T Flip Flop
3. D Flip Flop.

1. R-S Flip Flop. :- In the fig (a) show a R-S F/F and table + is show a Table of a R-S flip flop

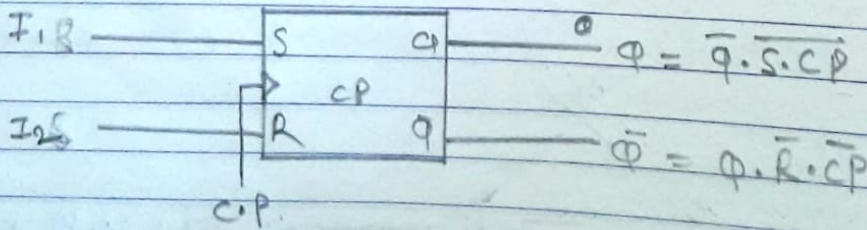
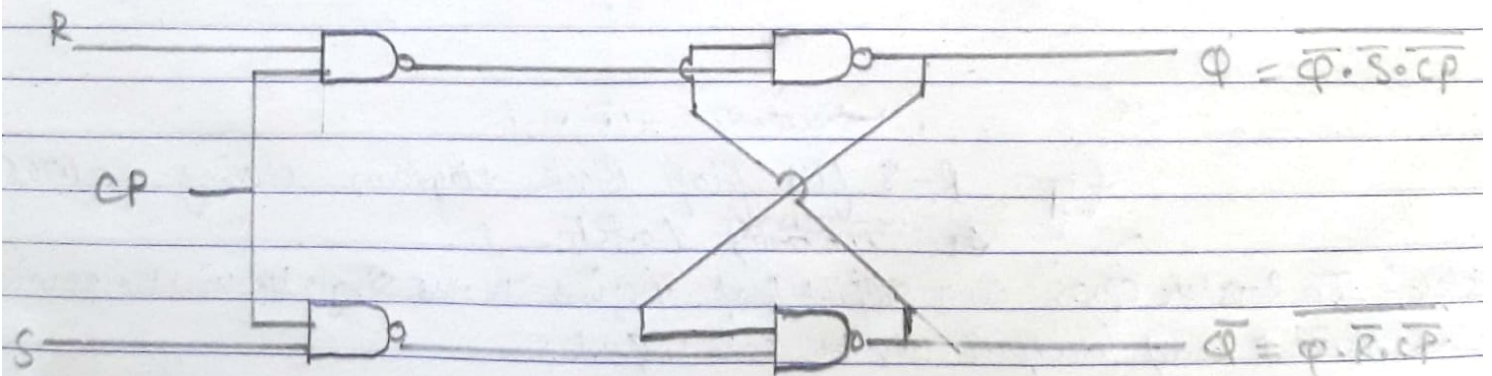


fig (a) R-S flip flop.

Bit.	Bits	$Q_{m+1}$
0	0	$Q_m$
0	1	0
1	0	1
1	1	Indeterminate

Table 1. RS flip flop table.

R-S flip flop using nand gate. Block diagram.



fig(1) - Block diagram of R-S F/F using NAND gates.

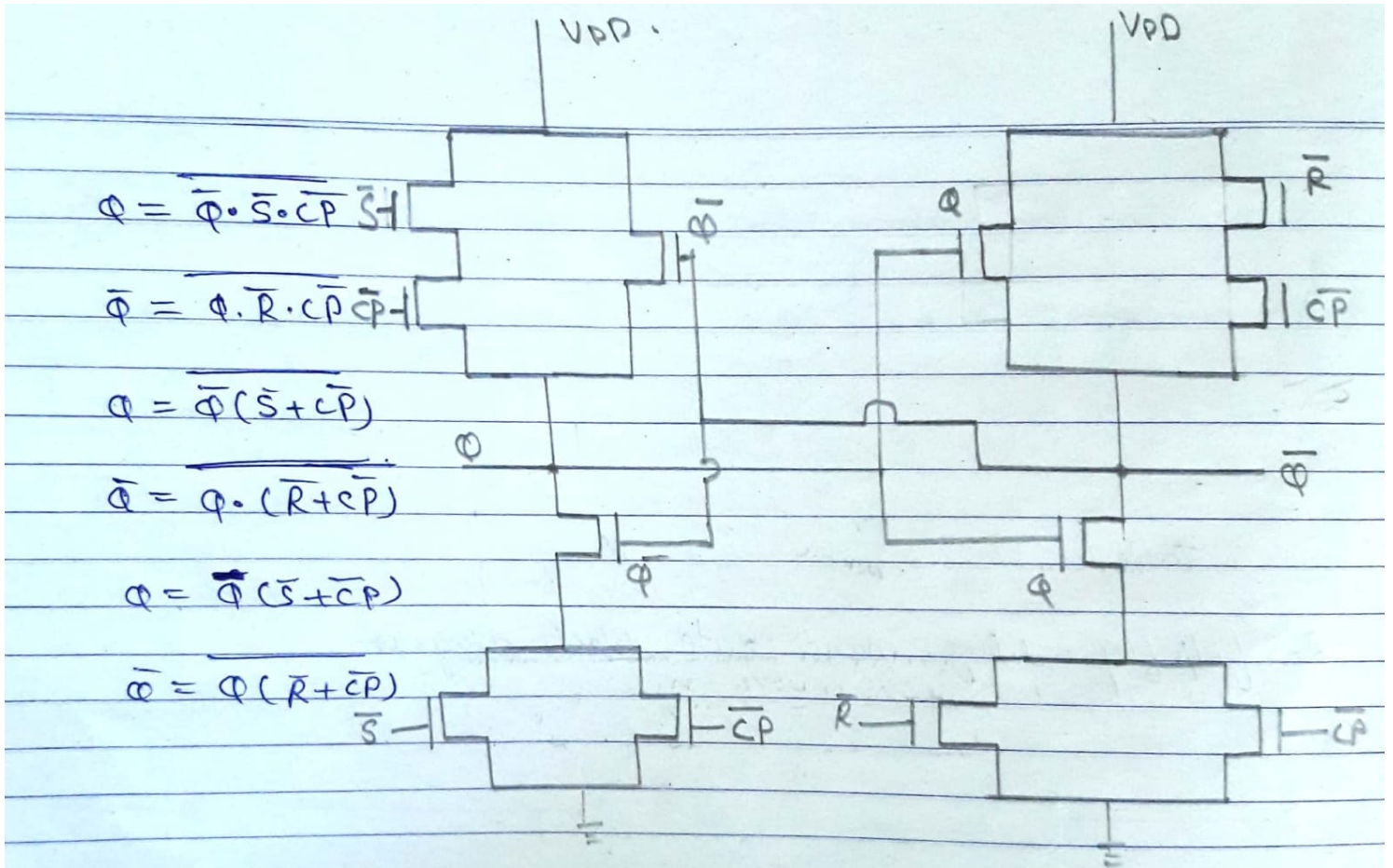
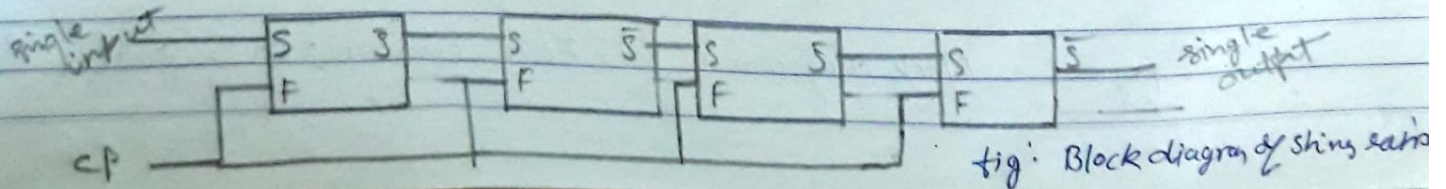


fig. R-S flip flop Block diagram using CMOS memory Latch

Resistors:- In Resistive CMOS in a shift flip flop. is given. In the single ip will be given with clock pulse F and output will be same give.



- Classification.
1. Single input Parallel output (SIPO)
  2. Single input Serial output (SISO)
  3. Single output Parallel input (SOPI)
  4. Single output Serial input (SOSI)

## Q.2. Enhancement mode transistor action:-

The fig (a) will show of an enhancement mode MOS transistor action. i) when the  $V_{GS} > V_{th}$  the gain the enhancement will be established and the  $V_{DS} = 0$  the drain and source between the current will be zero.

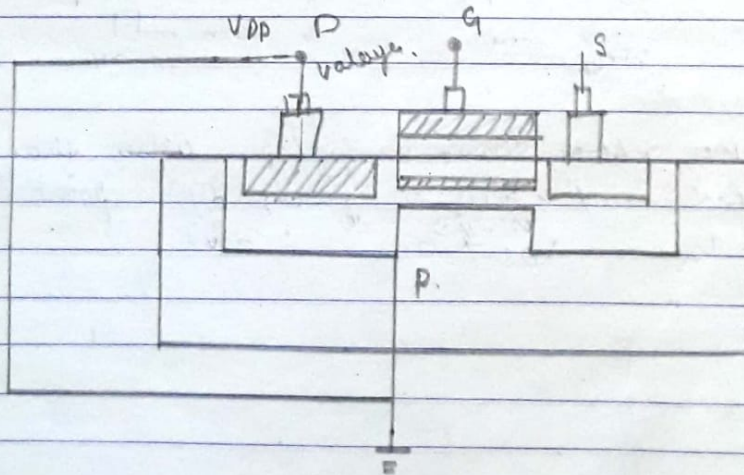
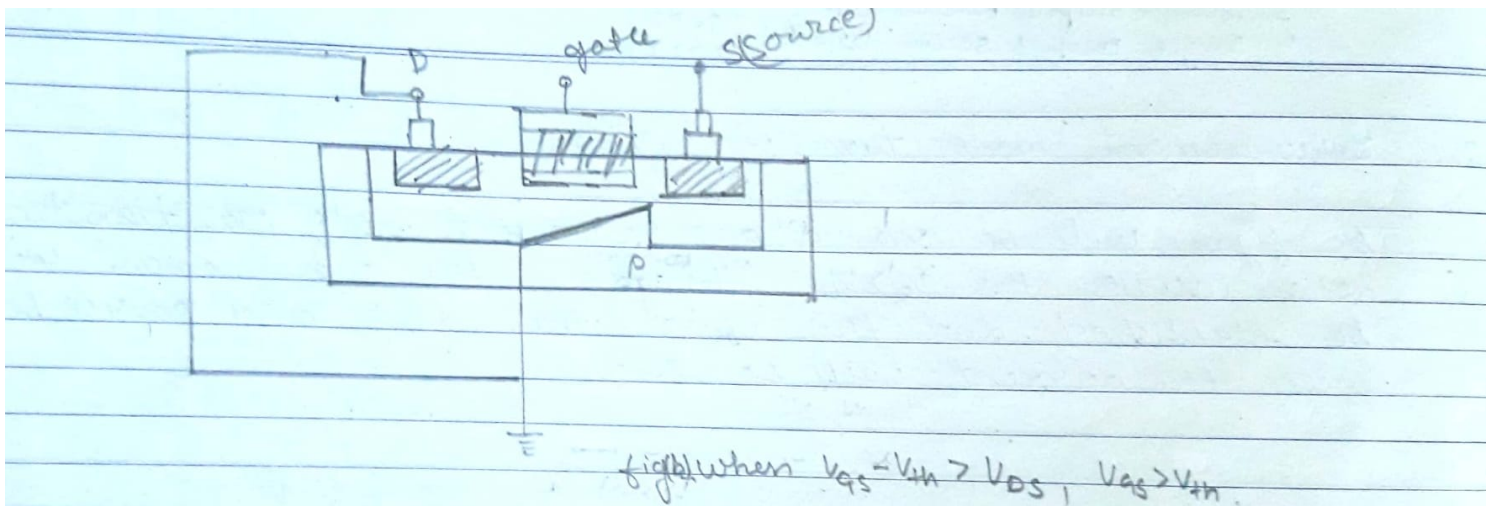
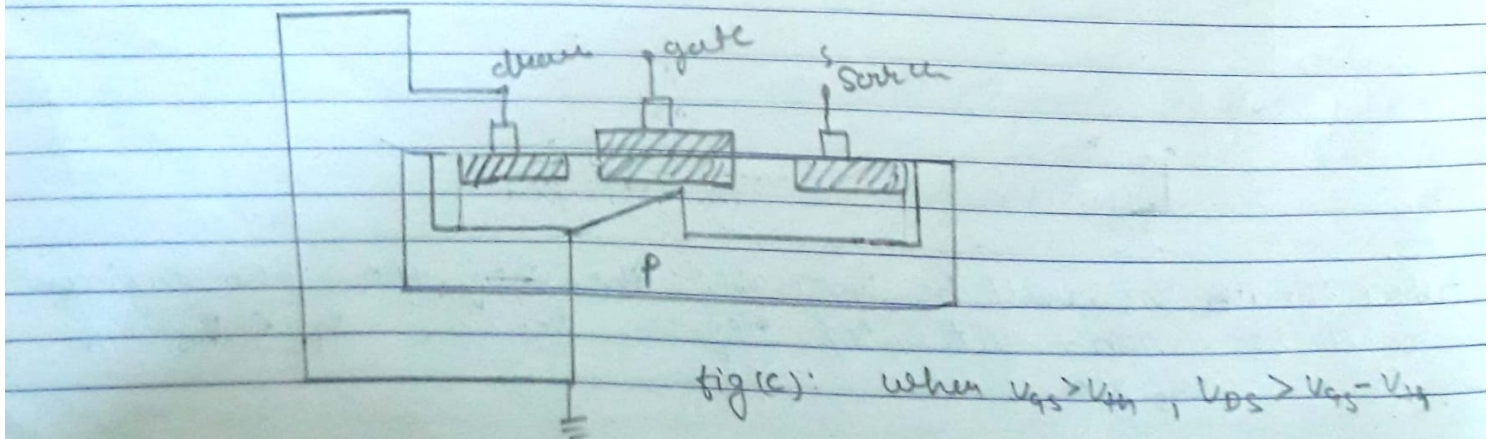


fig (a) when  $V_{GS} > V_{th}$  ,  $V_{DS} = 0$ .

ii) when the  $V_{GS}$  will be increased the  $V_{DS}$  will be increased then the region will be non-saturated region.  $V_{GS} > V_{th}$  ,  $V_{DS} < V_{GS} - V_{th}$   
 $V_{DS} \neq 0$ .



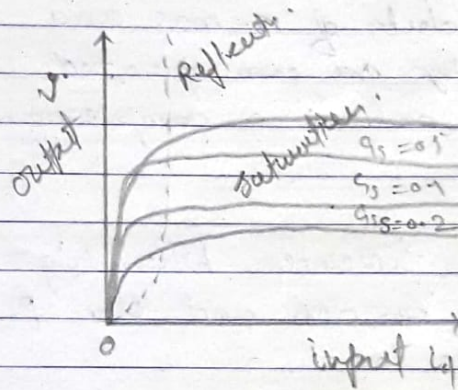
i) When the  $V_{ds} > V_{gs} - V_{th}$  ~~then show~~ in fig(c). ~~when~~ show the given region will be saturated and give a 'pinch off' point in the.  
 $V_{ds} > V_{gs} - V_{th}$ ,  $V_{gs} \neq 0$



Characteristics of enhancement mode transistor action.

i)  $I_d - V$  characteristics :-

$$I_d = \frac{1}{2} \mu_n C_{ox} \left( \frac{W}{L} \right) V_{ds}^2$$



ii) Pinch off Behaviour :-

In the pinch off behaviour, the  $V_{ds} > V_{gs} - V_{th}$  then the  $x \leq L$  to give a saturated region and this situation is called a 'Pinch off'.

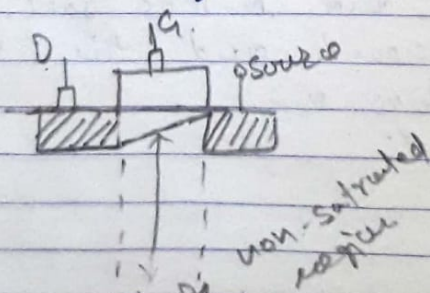


fig: Non-saturated region.  $V_{ds} < V_{gs} - V_{th}$ .

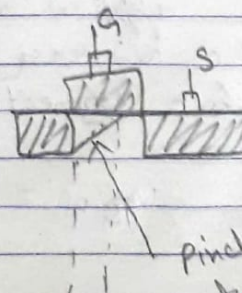


fig: Saturated region  $V_{ds} > V_{gs} - V_{th}$ .



Ques 3. CMOS Inverter :- In the transmission the enhancement duty of n-mos and the enhancement duty of P-mos transistor are operated in a complementary. This process are called a complementary MOS (CMOS) inverter.

working:-

In the CMOS inverter, when high voltage then the n-mos transistor are ON and the P-mos transistor are OFF while act the load.

When the low voltage then the P-mos transistor are ON and the N-mos transistor are OFF while a act of the load.

circuit operation: In the CMOS transistor, i/p voltage is applied the P-mos and N-mos. gate  $V_{gs}$ . The N-mos is a ground and the P-mos is a connect to a voltage  $V_{DD}$ .

$$V_{gs, n} = V_{ip}$$

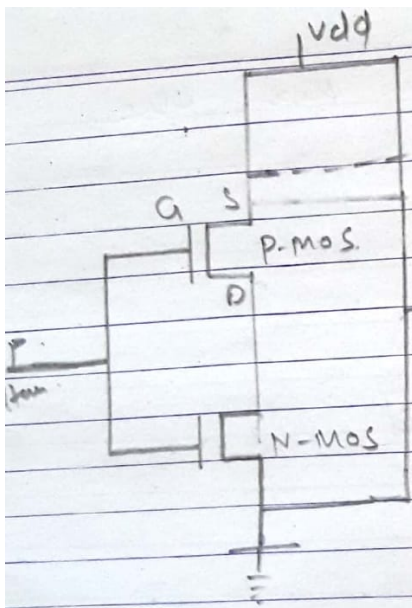


fig :- CMOS Inverter PMOS and N-MOS-transistor.

$$V_{ds, n} = V_{out}$$

$$V_{gs, P} = V_{DD} - V_{sp}$$

$$V_{gs, P} = V_{in} - V_{out}$$

$$V_{gs, P} = -(V_{out} - V_{in})$$

$$V_{gs, P} = -(V_{DD} - V_{in})$$

$$V_{ds, P} = -(V_{DD} - V_{out}).$$

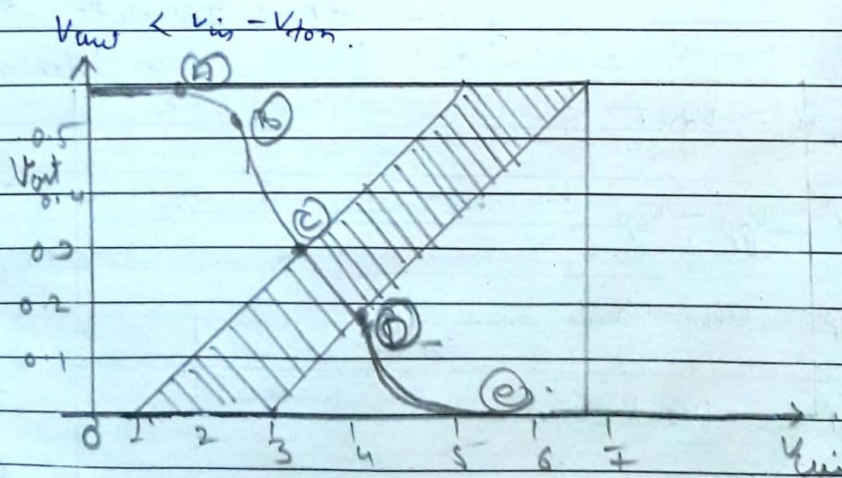
i) when n-mos transistor are on. then the

$$V_{dsn} \geq V_{gs} - V_{thn}$$

$$V_{out} > V_{in} - V_{thn}$$

ii) when p-mos transistor are worked

$$V_{dsn} \leq V_{gs} - V_{thn}$$



fig' - graphically representation of a CMOS inverter